

The TCAQ is a high voltage, high current disc pack SCR employing a high di/dt gate structure. This gate design allows the SCR to be reliably operated at high di/dt and dv/dt conditions in various phase control applications.

FEATURES:

- Low On-State Voltage
- High di/dt Capability
- High dv/dt Capability
- Hermetic Ceramic Package
- Excellent Surge and I²t Ratings

APPLICATIONS:

- DC Power Supplies
- Motor Controls
- SS Contactors

ORDERING INFORMATION

Select the complete 12 digit Part Number using the table below.
EXAMPLE: TCAQ28340HDH is a 2800V-3400A SCR with 250ma IGT and 12 inch gate and cathode potential leads.

PART	Voltage Rating V _{DRM} -V _{RSM}	Voltage Code	Current Rating I _{avg}	Current Code	Turn-Off T _q	Gate I _{GT}	Leads
TCAQ	2200	22	3400	34	0	H	DH
	2500	25					
	2800	28			500us (typ.)	250ma (max)	12"

Absolute Maximum Ratings

Characteristic	Symbol	Rating	Units
Repetitive Peak Voltage	$V_{DRM}-V_{RRM}$	2800	Volts
Average On-State Current, $T_C=70^{\circ}C$	$I_{T(Avg.)}$	3400	A
RMS On-State Current, $T_C=70^{\circ}C$	$I_{T(RMS)}$	5341	A
Average On-State Current, $T_C=54^{\circ}C$	$I_{T(Avg.)}$	4100	A
RMS On-State Current, $T_C=54^{\circ}C$	$I_{T(RMS)}$	6440	A
Peak One Cycle Surge Current, 60Hz, $V_R=0V$	I_{TSM}	60,000	A
Peak One Cycle Surge Current, 50Hz, $V_R=0V$	I_{TSM}	56,568	A
Fuse Coordination I^2t , 60Hz	I^2t	1.50E+07	A ² s
Fuse Coordination I^2t , 50Hz	I^2t	1.60E+07	A ² s
Critical Rate-of-Rise of On-State Current	di/dt	300	A/us
Repetitive			
Critical Rate-of-Rise of On-State Current	di/dt	600	A/us
Non-Repetitive			
Peak Gate Power, 100us	P_{GM}	16	Watts
Average Gate Power	$P_{G(avg)}$	5	Watts
Operating Temperature	T_j	-40 to+125	$^{\circ}C$
Storage Temperature	$T_{Stg.}$	-50 to+150	$^{\circ}C$
Approximate Weight		4.6	lb
		2.09	Kg
Mounting Force		9,000 - 12,000	lbs
		40 - 53	Knewtons

Electrical Characteristics, Tj=25°C unless otherwise specified

Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Repetitive Peak Forward Leakage Current	I_{DRM}	Tj=125°C, V_{DRM} =Rated			250	ma
Repetitive Peak Reverse Leakage Current	I_{RRM}	Tj=125°C, V_{RRM} =Rated			250	ma
Peak On-State Voltage	V_{TM}	Tj=125°C, I_{TM} =3000A			1.34	V
V_{TM} Model, Low Level	V_0	Tj=125°C			0.915	V
$V_{TM} = V_0 + r \cdot I_{TM}$	r	15% $I_{TM} - I_{TSM}$			1.40E-04	Ω
V_{TM} Model, High Level	V_0	Tj=125°C			1.038	V
$V_{TM} = V_0 + r \cdot I_{TM}$	r	$\pi \cdot I_{TM} - I_{TSM}$			1.05E-04	Ω
V_{TM} Model, 4-Term	A	Tj=125°C			0.150	
$V_{TM} = A + B \cdot \ln(I_{TM}) +$	B	15% $I_{TM} - I_{TSM}$			0.140	
$C \cdot (I_{TM}) + D \cdot (I_{TM})^{1/2}$	C				0.000115	
	D				-0.005	
Turn-On Delay Time	t_d	$V_D = 0.5 \cdot V_{DRM}$ Gate Drive: 40V - 20 Ω		2.5		us
Turn-Off Time	t_q	Tj=125°C $dv/dt = 20V/us$ to 80% V_{DRM}			400	us
$dv/dt_{(crit)}$	dv/dt	Tj=125°C Exp. Waveform $V_D = 80\%$ Rated	1000			V/us
Gate Trigger Current	I_{GT}	Tj=25°C $V_D = 12V$	30	100	250	ma
Gate Trigger Voltage	V_{GT}		0.8	2.0	4.5	V
Peak Reverse Gate Voltage	V_{GRM}				5	V

Thermal Characteristics

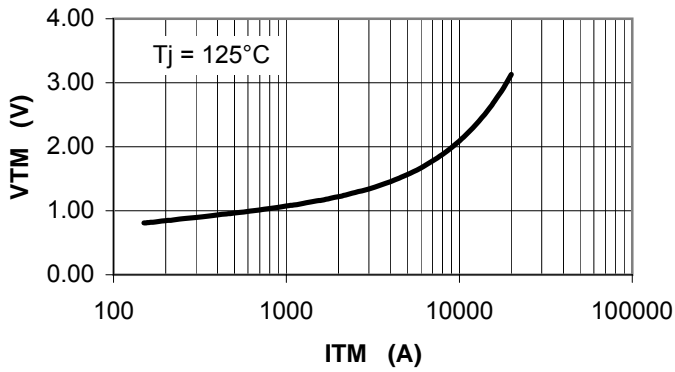
Characteristic	Symbol	Test Conditions	Rating			Units
			min	typ	max	
Thermal Resistance						
Junction to Case	$R\theta_{jc}$	Double side cooled		0.007	0.008	°C/Watt
Case to Sink	$R\theta_{cs}$	Double side cooled		0.0015	0.002	°C/Watt

Thermal Impedance Model $Z\theta_{jc}$ Double side cooled

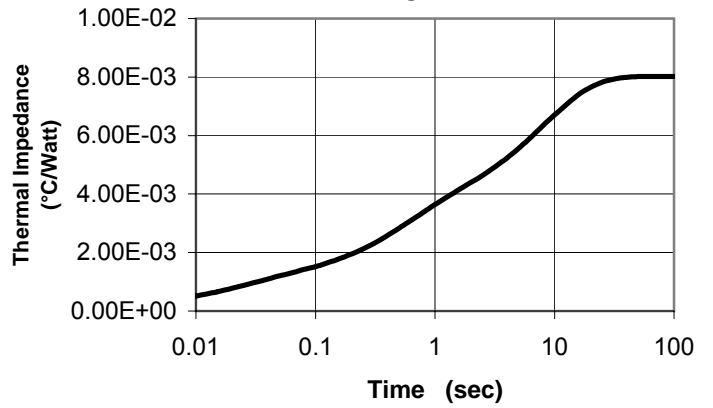
$$Z\theta_{jc}(t) = \sum(A(N) \cdot (1 - \exp(-t/\text{Tau}(N))))$$

where:	N =	1	2	3	4
	A(N) =	1.43E-04	9.08E-04	2.37E-03	4.60E-03
	Tau(N) =	2.62E-03	2.31E-02	5.00E-01	8.00E+00

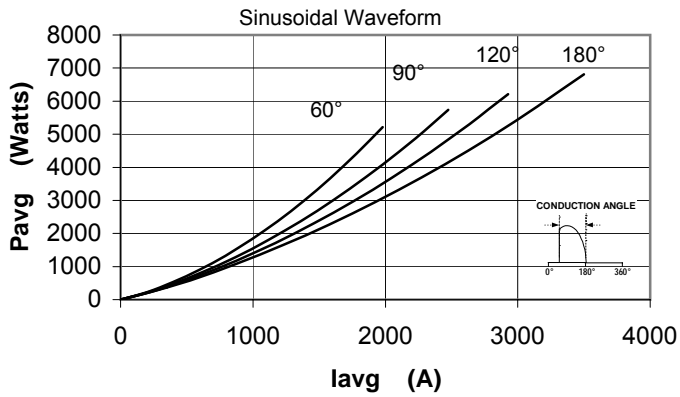
Maximum On-State Voltage Drop



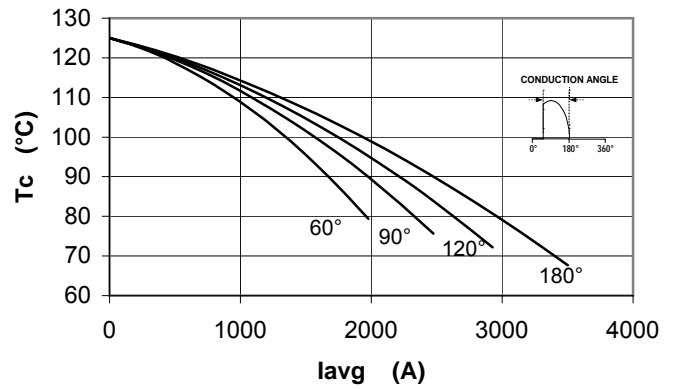
MAXIMUM TRANSIENT THERMAL IMPEDANCE



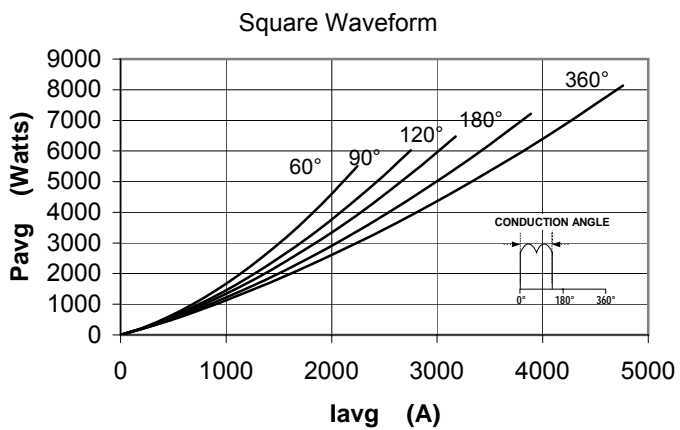
Maximum On-State Power Dissipation



Maximum Allowable Case Temperature



Maximum On-State Power Dissipation



Maximum Allowable Case Temperature

